行政院國家科學委員會專題研究計畫成果報告

橢圓偏光儀之異向晶體量測 計畫編號:NSC 88-2112-M-009-040 執行期限:87年8月1日至88年7月31日 主持人:趙于飛 國立交通大學光電所

一、中文摘要

本計畫除了延續前計畫利用石英將入 射角的偏差更正後量測一單軸異向晶體 YV04. 本計畫量測此晶體的正常及其異常 折射率外並量得該晶體的光軸位置,結果 與廠商規格相合。

關鍵詞:橢圓偏光儀,雙折射晶體

Abstract

 This report continues our previous work on measuring the optical properties of a uniaxial crystal. We corrected the beam deviation using a Quartz crystal and measure the ordinary and extraordinary refractive indices of YVO4 and compared with vendor's specifications. We also measured the orientation of its optical axis.

Keywords: Ellipsometry, birefringence

\equiv \cdot Introduction

According to our previous study [1], we are able to measure the incident beam deviation in a rotating element ellipsometry by a quartz crystal. Because this calibration, we are able to construct a system to measure the optical axis and refractive indices of a uniaxial crystal by two sheet polarizers. Besides the ordinary and extraordinary refractive indices, we also applied this technique to measure the angle between the normal to the cleavage plane and optic axis of a Yttrium Or-thovanadate (YVO4).

 In this study, we proved that this PSA ellipsometry not only can measure the isotropic material it also can be used as rotating element ellipsometry for measure the optical properties of uniaxial crystals.

Ξ \cdot Theory, experiment and result

The reflected $\chi_{\rm r}$ and incident $\chi_{\rm i}$ polarization states are related by [2]

$$
\chi_r = \frac{(r_{sp}/r_{ss}) + \chi_i}{(r_{pp}/r_{ss}) + (r_{ps}/r_{ss}) \cdot \chi_i}
$$

(1)

where r_{xx} is the Fresnel reflection coefficient for the parallel (p, i.e. x) and perpendicular(s, i.e. y) polarizations. The analytical expressions of these Fresnel reflection coefficients for uniaxial crystals in the Appendix. The complex pseudoreflectance ratio was defined [2] as for anisotropic media, while in general ρ is defined as [3]

$$
\rho=\tan\psi e^{i\Delta},
$$

$$
\tan^2 \psi = \left|\frac{\chi_i}{\chi_r}\right|^2
$$

thus

 (2)

Since the cross terms vanish in an isotropic medium, tan ψ [3] equals $|r_{\text{pp}}/r_{\text{ss}}|$, which is the conventional expression for the ellipsometric

parameter. The reflection geometry for a uniaxial crystal is shown in Fig. 1.

> Figure 1. The reflection geometry: θ_i is the incident angle, xy plane is the

reflecting face of the crystal, zx plane is the incident plane, the z axis is the normal line. OA is the optical axis of the crystal.

A simple model for anisotropic crystals was proposed by Aspnes [4]: the measured ellipsometric parameters for a particular θ_a equal those of the effective isotropic sample whose refractive index is given by its dielectric tensor projection onto the sample surface along the incident direction. This implies that

$$
\tan^2 \Psi = \frac{2 \pi}{2 \pi} \tag{3}
$$

where I_{rp} represents the reflected intensity parallel to the incident plane and I_x represents the reflected intensity perpendicular to the incident plane, for $P =$ 45[°], i.e. $\chi_i = 1$. According to equation (3), one can obtain tan ψ simply by measuring the reflected intensities I_{rp} and I_{r} . If the optical

axis of a nonabsorbent uniaxial crystal is parallel to the reflection surface, i.e. $\theta_{\rm c}$ = 90°, then the ellipsometric parameter ψ can be characterized by a twofold symmetry with respect to θ_a , the azimuthal angle. Since we were only interested in determining the AI in a PSA ellipsometry, such as shown in Fig. 2, we simulated the ellipsometric parameter function $\psi(\theta_a)$ for a uniaxial crystal with n_o and n_a as its ordinary and extraordinary refractive indices, respectively. Furthermore, we assume the optical axis of the sample crystal is parallel to the reflection surface so as to obtain the twofold symmetry for comparison.

 Fig. 2 A schematic set-up of the PSA ellipsometer: L, light source (He-Ne laser); P, polarizer; A, analyzer; D, detector.

The function $\psi(\theta_a)$ is simulated for $\chi_i = i$, i.e. $P = 45^{\circ}$, and optimized [5] by $\chi_i = -i$, i.e. $P = -45^{\circ}$, to eliminate the error caused by the misalignment of the polarizer, according to equation (3), one can obtain

$$
\tan \psi = \left[\frac{I_{p}}{I_{s}}\right]_{P=45^{\circ}} \frac{I_{p}}{I_{s}}\right)_{P=-45^{\circ}} \Big]^{1/4}.
$$
\n(4)

The measured and simulated values are compared in Fig. 2

44.94° (line \mathbb{I} calculated •: measured) and $\theta_a = 7.24^{\circ}$.

$\overline{\text{m}}$ \cdot Conclusion and discussion

The angle (θ_c) between the normal to the cleavage plane and the optic axis of YVO4 crystal at $\theta_i = 44.94^{\circ}$ was obtained to be 136.01° and $θ_4$ (Fig. 1) to be 7.24 ± 0.01°, as shown in Fig. 3, while θ_c was specified as 135° from the vendor (CASIX). In addition to determining the deviation of incident angle in a rotating element ellipsometry, the following three parameters can be obtained by fitting the measured tan ψ to the analytic solution of uniaxial crystals: the absolute value of n_e , n_e and directions of optical axis $(\theta_a \text{ and } \theta_c)$ in the laboratory frame. Since the resolving power of the system can be increased as the incident angle moves closer to the Brewster angle (the reflected intensity at 50° will be about 0.4% of the incident intensity), the system can be improved by using a sensitive detector or a higher power light source. It is our interest to extend the current experimental system to measure a material which consists of both linear and circular birefringence.

五、 Acknowledgement

 We like to thank NSC for grating the research. This research and last one has been combined and published in Journal of Physics: D [8]

\sim Appendix

This appendix is cited from reference [6] and [7]. The reflection geometry is shown in Fig. 1. The direction of optical axis is specified by angles θ_a and θ_c relative to the laboratory xyz, if \vec{c} is the unit vector of optical axis, we can express it as

$$
\vec{c} = c\alpha c\beta c\gamma c,
$$

where $\alpha = \cos \theta_a \sin \theta_c$, $\beta = \sin \theta_a \sin \theta_c$ and $\gamma = \cos \theta_c$. Let the incident wave vector be \vec{i} + \vec{c} i^c, where K= k n_isin θ_L , q₁= k n_icos θ_h for a wave number $\;k\;$ $=\frac{\omega}{c}$ at incident angle θ_i . According to reference 11, we summarized the Fresnel reflection coefficients for uniaxial crystals of ordinary refractive index $n_e = \sqrt{\varepsilon_e}$ and extraordinary refractive index $n_e = \sqrt{\varepsilon_a}$ as follows;

$$
e_{ss} = {}_0c_{c_1} - c_e cAE_g^e - c_{c_1} - c_e cEE_g^o \nparallel E
$$

\n
$$
r_{\varphi} = {}_x n_i k cAE_x^e - BE_x^o dD
$$

\n
$$
e_{\text{pp}} = {}_{xc_1} {}_0c_{c_1} + c_e cE_x^o E_y^e - c_{c_1} + c_o cE_x^e E_y^o dE - x
$$

\n
$$
r_{ps} = {}_x n_i k c q_e - q_o cE_y^o E_y^e / D
$$

The ordinary and extraordinary modes have wave vector normal components q_{\bullet} , and q_{\bullet} related to the medium as

$$
q_e = c\sqrt{d} - \alpha\gamma K \Delta \varepsilon d c \varepsilon_o + \gamma^2 \Delta \varepsilon c,
$$

\n
$$
q_o = \varepsilon_o k^2 - K^2, \quad c_t = c_1 + c \tan \theta_i
$$

\nwhere $\Delta \varepsilon = \varepsilon_e - \varepsilon_o$, and
\n
$$
d = \varepsilon_o [\varepsilon_e (\varepsilon_o + \gamma^2 \Delta \varepsilon)] k^2 - (\varepsilon_e - \beta^2 \Delta \varepsilon) K^2]
$$

the corresponding electric field vectors \mathbf{E}^\bullet and \mathbf{E}^\bullet noted as

$$
\begin{array}{lcl} \mathbf{E}^{\bullet} = N_{\bullet}(-\beta q_{\bullet}, \ \alpha q_{\bullet} - \gamma K, \ \beta K) \ , \\ \mathbf{E}^{\bullet} & = & N_{\bullet}(\alpha q_{\bullet}^2 - \gamma q_{\bullet} K, \quad \beta \epsilon_{\bullet} k^2, \\ \gamma (\epsilon_{\bullet} k^2 - q_{\bullet}^2) - \alpha q_{\bullet} K), \end{array}
$$

where N_e , N_e are the normalization factor, respectively. For simplicity, we also state the collective parameters as follows;

$$
- = z \rightarrow + + \tan \theta_1 \text{ n} + z \rightarrow z
$$

\n
$$
1 = z \rightarrow + + \tan \theta_1 \text{ n} + z \rightarrow z
$$

\n
$$
D = zq_1 + q_e \text{ n}AE_e^e - zq_1 + q_o \text{ n}BE_e^e
$$

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